

### **Features**

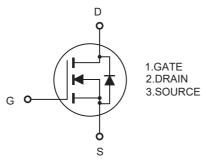
- · High Current Rating
- Lower R<sub>DS(ON)</sub>
- · Lower Capacitance
- Lower Total Gate Charge
- Tighter V<sub>SD</sub> Specifications
- · Avalanche Energy Specified
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free Available Upon Request By Adding Suffix "-HF"

# **Maximum Ratings**

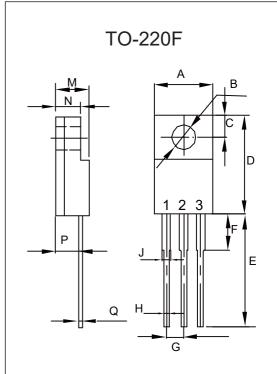
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 62.5°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Drain -Source Voltage	V <sub>DS</sub>	650	V
Gate -Source Volltage	V <sub>GS</sub>	±30	V
Drain Current-Continuous	I <sub>D</sub>	12.0	Α
Drain Current-Pulse <sup>(Note4)</sup>	I <sub>DM</sub>	48	Α
Power Dissipation	P <sub>D</sub>	2.0	W
Single Pulsed Avalanche Energy <sup>(note 1)</sup>	E <sub>AS</sub>	540	mJ
Maximum Lead Temperure for Soldering Purposes,1/8" from Case for 5 Seconds	T <sub>L</sub>	260	°C

### **Internal Structure**



# N-Channel Enhancement Mode Field Effect Transistor



DIMENSIONS					
DIM	INC	HES	MM		NOTE
Dilvi	MIN	MAX	MIN	MAX	NOTE
Α	0.392	0.421	9.96	10.70	
В	0.1	38	3.5	50	Ф
С	0.1	06	2.	70	TYP.
D	0.567	0.642	14.40	16.30	
E	0.5	20	13.	20	TYP.
F		0.177		4.50	
G	0.1	00	2.	54	TYP.
Н	0.020	0.035	0.50	0.90	
J	0.043	0.053	1.10	1.35	
M	0.169	0.201	4.30	5.10	
N		0.140		3.56	
Р	0.083	0.126	2.10	3.20	
Q	0.020	0.032	0.50	0.80	



# Electrical Characteristics @ 25°C (Unless Otherwise Noted)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Off Characteristics						I
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	650			V
Drain-Source Diode Forward Voltage <sup>(note2)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =12.0A			1.4	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			1.0	μA
Gate-Body Leakage Current, Forward <sup>(note2)</sup>	I <sub>GSSF</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =30V			100	- nA
Gate-Body Leakage Current, Reverse <sup>(note2)</sup>	I <sub>GSSR</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =-30V			-100	
On Characteristics(note2)						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	3.5	4.0	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		0.7	0.85	Ω
Dynamic Characteristics(note 3)						1
Input Capacitance	C <sub>iss</sub>			1800		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f=1MHz		200		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			25		-
Switching characteristics(note2,3,4)						
Total Gate Charge	$Q_g$			42	5	
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =520V,V <sub>GS</sub> =10V,I <sub>D</sub> =12A		8.6		_ nC
Gate-Drain Charge	$Q_{gd}$			21		_
Turn-On Delay Time(note 3)	t <sub>d(on)</sub>			30		
Turn-On Rise Time(note 3)	t <sub>r</sub>	V <sub>DD</sub> =325V,V <sub>GS</sub> =10V,		90		_
Turn-Off Delay Time(note 3)	$t_{d(off)}$	$R_G = 25\Omega, I_D = 12.0A$		160		ns -
Turn-Off Fall Time(note 3)	t <sub>f</sub>			90		
Drain-Source Diode Characteristics						
Maximum Continuous Drain-source Diode Forward Current	Is				12	А
Maximum Pulsed Drain-source Diode Forward Current	I <sub>SM</sub>				48	А

## Notes:

- 1. L=7.5mH,  $I_L$ =12A,  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , Starting  $T_J$ =25°C.
- 2. Pulse Test : Pulse width  $\!\!\!\! \leqslant\! 300\mu s,$  duty cycle  $\!\!\! \leqslant\! \! 2\%.$
- 3. These parameters have no way to verify.
- 4. Pulse width limited by maximum junction temperature



## **Curve Characteristics**

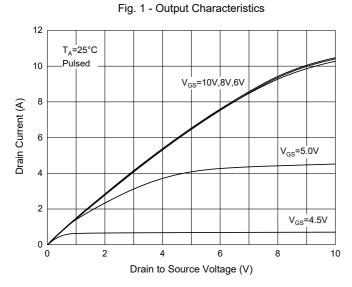


Fig. 2 - Transfer Characteristics

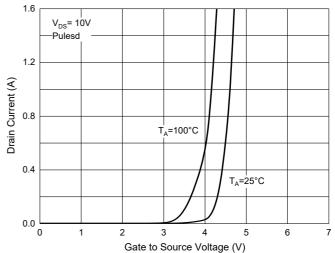


Fig. 3 - R<sub>DS(ON)</sub>—I<sub>D</sub>

1.2

1.0

0.8

V<sub>GS</sub>=10V

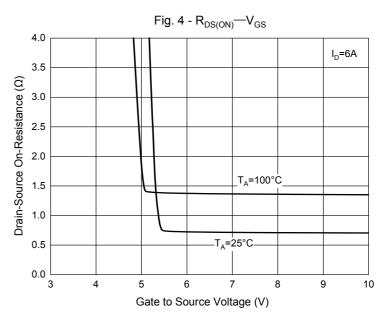
0.6

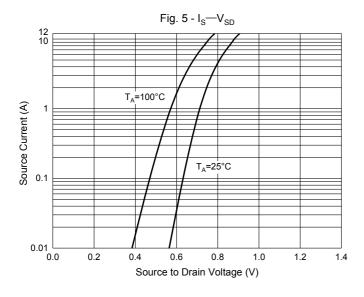
0.2

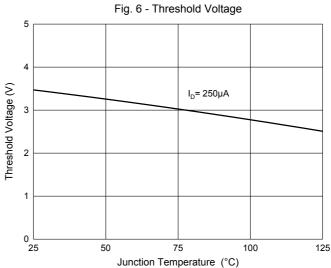
0.0

0 2 4 6 8 10 12

Drain Current (A)









### **Ordering Information**

Device	Packing
Part Number-BP	Bulk:50pcs/Tube,1Kpcs/Box,5Kpcs/Carton

Note: Adding "-HF" Suffix For Halogen Free, eg. Part Number-BP-HF

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